

NEC

9 GHz DIVIDE-BY-4 DYNAMIC PRESCALER

UPG503B

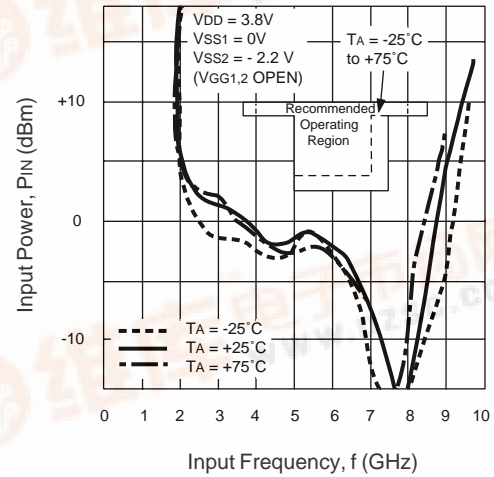
FEATURES

- **WIDE OPERATING FREQUENCY RANGE:**
 $f_{IN} = 3.5$ to 9.0 GHz ($T_A = 25^\circ\text{C}$)
- **DIVISION RATIO OF 4**
- **GUARANTEED OPERATING TEMPERATURE RANGE:**
 -25°C to $+75^\circ\text{C}$

DESCRIPTION

The UPG503B is a GaAs divide-by-4 prescaler that is capable of operating up to 9 GHz. It is designed to be used in the frequency synthesizers of microwave communication systems and measurement equipment. The UPG503B is a dynamic divider. It employs buffered FET logic (BFL). The UPG503B is available in a hermetic 8-lead ceramic flat package.

INPUT POWER vs. INPUT FREQUENCY



ELECTRICAL CHARACTERISTICS¹ ($T_A = 25^\circ\text{C}$, $V_{DD} = 3.8$ V, $V_{SS1} = 0$ V, $V_{SS2} = -2.2$ V)

PART NUMBER PACKAGE OUTLINE			UPG503B BF08		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
I _{DD}	Supply Current	mA	40	80	130
I _{SS1}	Sink Current ² I _{SS1} = I _{DD} - I _{SS2}	mA		27	
I _{SS2}	Sink Current ²	mA	21	53	93
f _{IN(U)}	Upper Limit of Input Frequency, P _{IN} = +9 to +10 dBm	GHz	8.6	9.0	
f _{IN(L)}	Lower Limit of Input Frequency, P _{IN} = +9 to +10 dBm	GHz		3.5	3.7
P _{IN}	Input Power, f _{IN} = 3.7 to 8.6 GHz f _{IN} = 5.0 to 7.4 GHz	dBm dBm	9.0 3.0		10.0 10.0
P _{OUT}	Output Power, f _{IN} = 8.6 GHz, P _{IN} = +10 dBm f _{IN} = 3.7 GHz, P _{IN} = +10 dBm	dBm dBm	0 0	3 3	
R _{TH}	Thermal Resistance, Channel to Case	°C/W			10

Note:

1. Device may exhibit low frequency spur typically below 150 Hz and -45 dBm.
2. Current is positive into the I_{DD} pin and returns through the I_{SS1} and I_{SS2} pins.



ELECTRICAL CHARACTERISTICS $T_A = 25^\circ\text{C}$ to $+75^\circ\text{C}$, $V_{DD} = 3.8\text{ V}$, $V_{SS1} = 0\text{ V}$, $V_{SS2} = -2.2\text{ V}$

PART NUMBER PACKAGE OUTLINE			UPG503B BF08		
SYMBOLS	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
I _{DD}	Supply Current	mA		80	
I _{SS1}	Sink Current ¹ I _{SS1} = I _{DD} - I _{SS2}	mA		27	
I _{SS2}	Sink Current ¹	mA		53	
f _{IN(U)}	Upper Limit of Input Frequency, P _{IN} = +9 to +10 dBm	GHz	8.0		
f _{IN(L)}	Lower Limit of Input Frequency, P _{IN} = +9 to +10 dBm	GHz			4.0
P _{IN}	Input Power, f _{IN} = 4.0 to 8.0 GHz f _{IN} = 5.0 to 7.0 GHz	dBm dBm	9.0 4.0		10.0 10.0
P _{OUT}	Output Power f _{IN} = 8.0 GHz, P _{IN} = +10 dBm f _{IN} = 4.0 GHz, P _{IN} = +10 dBm	dBm dBm	-1.0 -1.0	2.0 2.0	

Note:

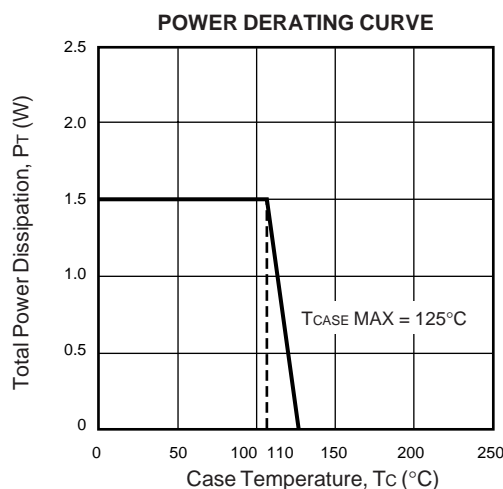
1. Current is positive into the I_{DD} pin and returns through the I_{SS1} and I_{SS2} pins.

ABSOLUTE MAXIMUM RATINGS¹ ($T_A = 25^\circ\text{C}$)

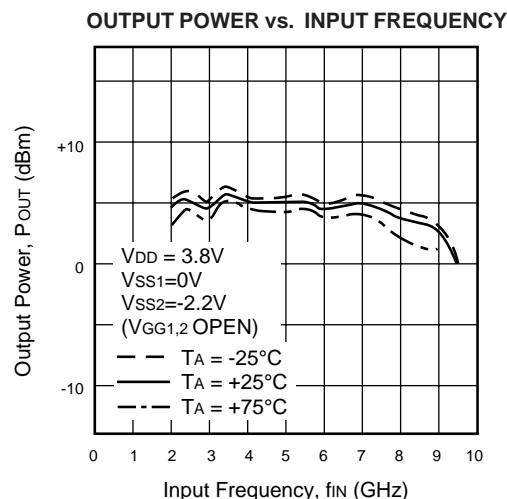
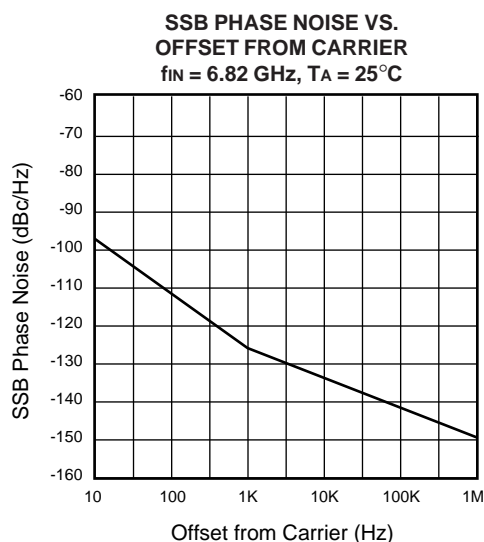
SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{DD} -V _{SS1}	Supply Voltage	V	5.0
V _{SS2} -V _{SS1}	Supply Voltage	V	-5.0
P _{IN}	Input Power	dBm	13
P _T	Total Power Dissipation ²	W	1.5
T _{STG}	Storage Temperature	°C	-65 to +175
T _c	Case Temperature	°C	-65 to +125

Notes:

1. Operation in excess of any one of these conditions may result in permanent damage.
2. $T_c \leq 125^\circ\text{C}$

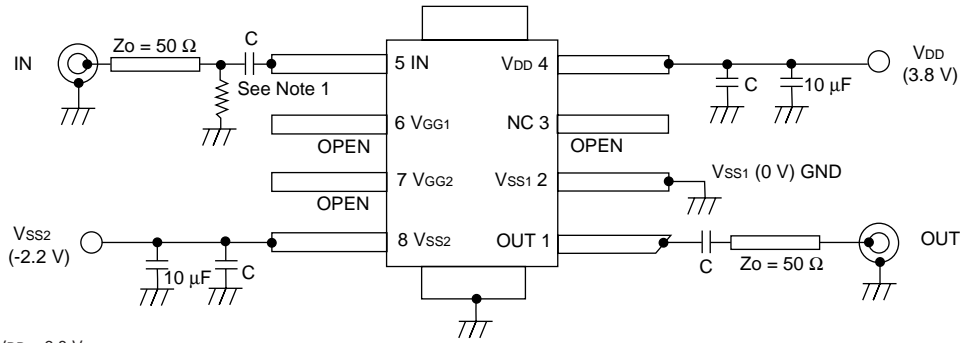


TYPICAL PERFORMANCE CURVES ($T_A = 25^\circ\text{C}$)



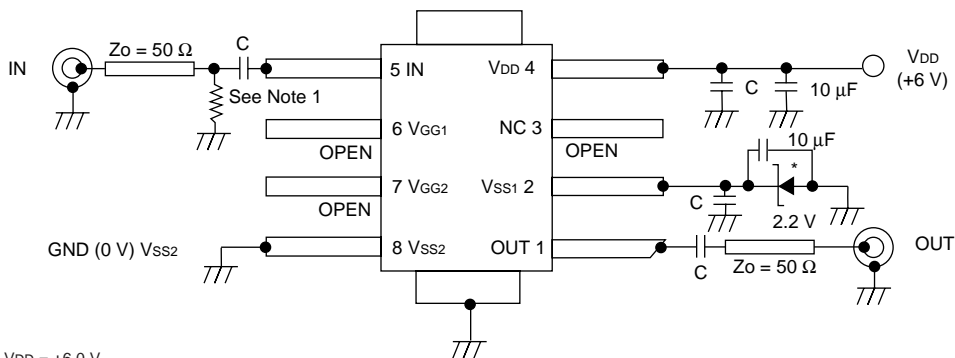
POWER SUPPLY CONFIGURATIONS (V_{GG1} and V_{GG2} are normally open)

CONFIGURATION 1 2 Bias Supply



V_{DD} = 3.8 V
V_{SS1} = 0 V (GND)
V_{SS2} = -2.2 V
C: 1000 - 5000 pF Chip Capacitor

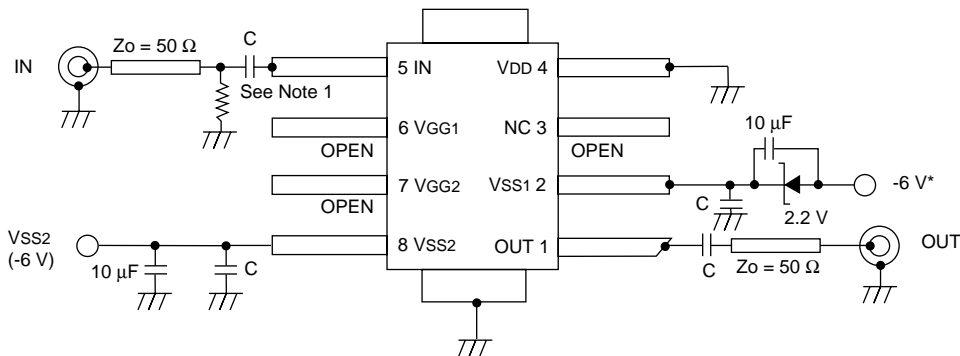
CONFIGURATION 2 Single Positive Bias Supply



V_{DD} = +6.0 V
V_{SS2} = 0 V (GND)
C: 1000 - 5000 pF Chip Capacitor

* V_{SS1} should be connected to GND through a 2.2 V Zener Diode (RD2.2FB or IN3394).

CONFIGURATION 3 Single Negative Bias Supply



V_{DD} = 0 V (GND)
V_{SS2} = -6 V
C: 1000 - 5000 pF Chip Capacitor

* For V_{SS1}, the bias voltage of -6.0 should be applied through a 2.2 V Zener Diode (RD2.2FB or IN3394).

Notes:

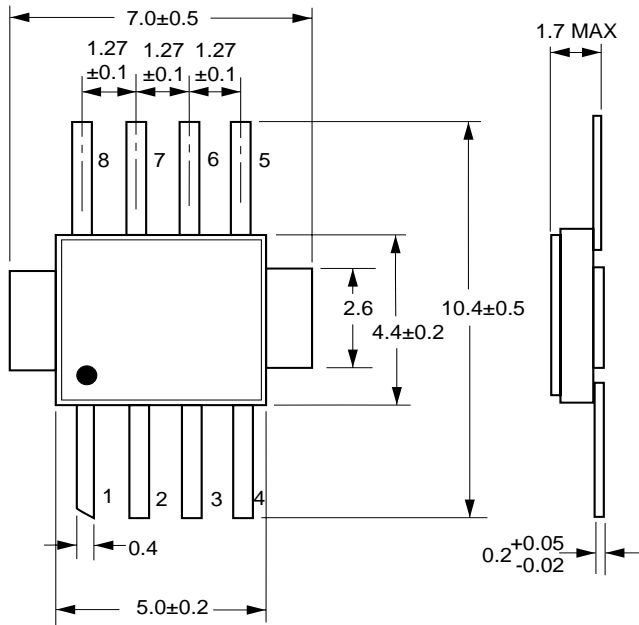
1. Because of the high internal gain and gain compression of the UPG503B, the device is prone to self-oscillation in the absence of an RF input signal. This self-oscillation can be suppressed by either of the following means:

- Add a shunt resistor to the RF input line. Typically a resistor value between 50 and 1000 ohms will suppress the self-oscillation (see the test circuit schematic).
- Apply a negative voltage through a 1000 ohm resistor to the normally open V_{GG1} connection. Typically voltages between 0 and -9 volts will suppress the self-oscillation.

Both of these approaches will reduce the input sensitivity of the device (by as much as 3 dB for a 50 ohm shunt resistor), but otherwise have no effect on the reliability or electrical characteristics of the device.

OUTLINE DIMENSIONS (Units in mm)

UPG503B
PACKAGE OUTLINE BF08



LEAD CONNECTIONS:

- | | |
|---------------------|---------------------|
| 1. OUTPUT | 5. INPUT |
| 2. V _{SS1} | 6. V _{GG1} |
| 3. NC* | 7. V _{GG2} |
| 4. V _{DD} | 8. V _{SS2} |

* No Connection